

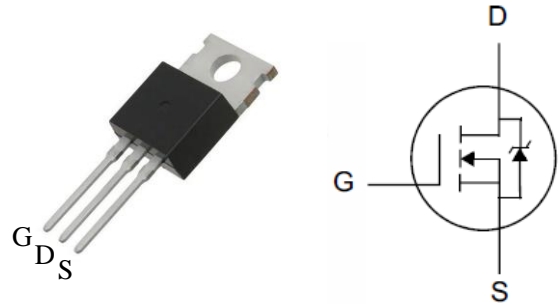
General Features

- Proprietary New Trench Technology
- $R_{DS(ON),typ.}=8.5m\Omega@V_{GS}=10V$
- Low Gate Charge Minimize Switching Loss
- Fast Recovery Body Diode

BV_{DSS}	$R_{DS(ON),typ.}$	I_D
150V	8.5m Ω	120A

Applications

- DC/DC Converter
- Motor Control
- Synchronous Rectification


Ordering Information

Part Number	Package
IRFB4115PBF-CN	TO-220

TO-220

Package No to Scale

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	IRFB4115PBF-CN	Unit
V_{DSS}	Drain-to-Source Voltage ^[1]	150	V
V_{GSS}	Gate-to-Source Voltage	± 20	
I_D	Continuous Drain Current	120	A
	Continuous Drain Current @ $T_C=100^{\circ}C$	84	
I_{DM}	Pulsed Drain Current at $V_{GS}=10V$ ^[2]	380	
E_{AS}	Single Pulse Avalanche Energy $L=1mH$	450	mJ
P_D	Power Dissipation	208	W
	Derating Factor above $25^{\circ}C$	0.67	W/ $^{\circ}C$
T_L T_{PAK}	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10 seconds, Package Body for 10 seconds	300 260	$^{\circ}C$
T_J & T_{STG}	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	IRFB4115PBF-CN	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.6	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62	

Electrical Characteristics

OFF Characteristics $T_J = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	150	--	--	V	$V_{GS}=0V, I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	--	--	1	μA	$V_{DS}=150V, V_{GS}=0V$
		--	--	100		$V_{DS}=150V, V_{GS}=0V, T_J=125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Current	--	--	+100	nA	$V_{GS}=+20V, V_{DS}=0V$
		--	--	-100		$V_{GS}=-20V, V_{DS}=0V$

ON Characteristics $T_J = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	8.5	10.5	$m\Omega$	$V_{GS}=10V, I_D=20A$
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$

Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance	--	2980	--	pF	$V_{GS}=0V, V_{DS}=75V, f=1.0MHz$
C_{rSS}	Reverse Transfer Capacitance	--	4.0	--		
C_{oss}	Output Capacitance	--	283	--		
R_G	Gate Series Resistance	--	2.0	--	Ω	$f=1.0MHz$
Q_g	Total Gate Charge	--	39	--	nC	$V_{DD}=75V, I_D=20A, V_{GS}=0 \text{ to } 10V$
Q_{gs}	Gate-to-Source Charge	--	13	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	6.8	--		

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
td(ON)	Turn-on Delay Time	--	21	--	ns	V _{DD} =75V, I _D =20A, V _{GS} = 10V R _G =3.0Ω
trise	Rise Time	--	7.6	--		
td(OFF)	Turn-Off Delay Time	--	37	--		
tfall	Fall Time	--	6.7	--		

Source-Drain Body Diode Characteristics T_J=25°C unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
I _{SD}	Continuous Source Current ^[2]	--	--	120	A	Integral PN-diode in MOSFET
I _{SM}	Pulsed Source Current ^[2]	--	--	380		
V _{SD}	Diode Forward Voltage	--	--	1.2	V	I _S =40A, V _{GS} =0V
trr	Reverse recovery time	--	113	--	ns	V _{GS} =0V, I _F =20A, diF/dt=100A/μs
Qrr	Reverse recovery charge	--	141	--	nC	

Note:

- [1] T_J=+25°C to +150°C .
- [2] Repetitive rating; pulse width limited by maximum junction temperature.
- [4] Pulse width≤380μs; duty cycle≤2%.

Typical Characteristics

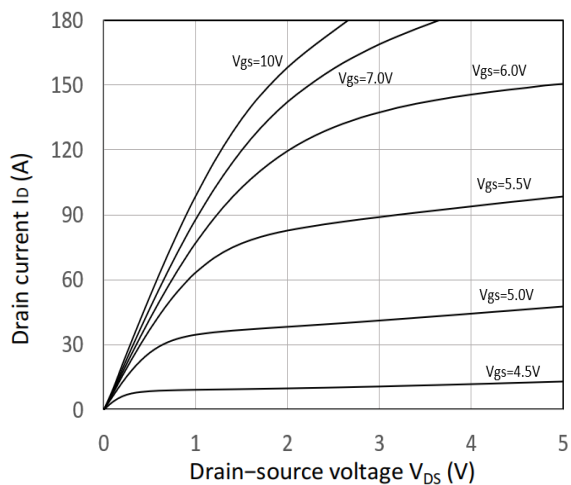


Figure 1. Output Characteristics

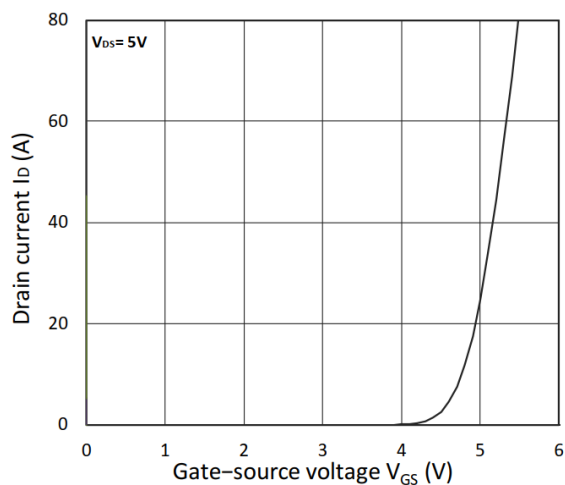


Figure 2. Transfer Characteristics

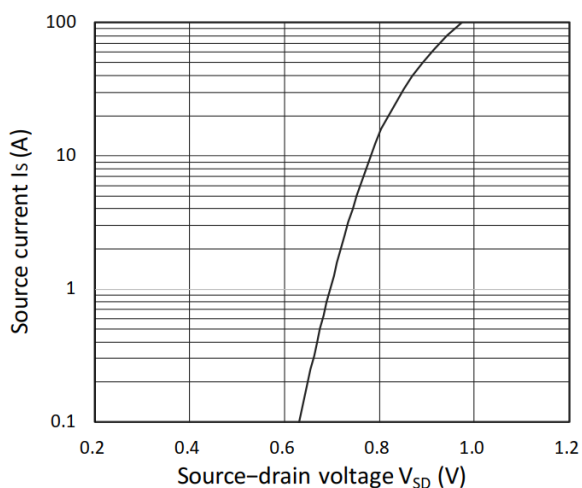


Figure 3. Forward Characteristics of Reverse

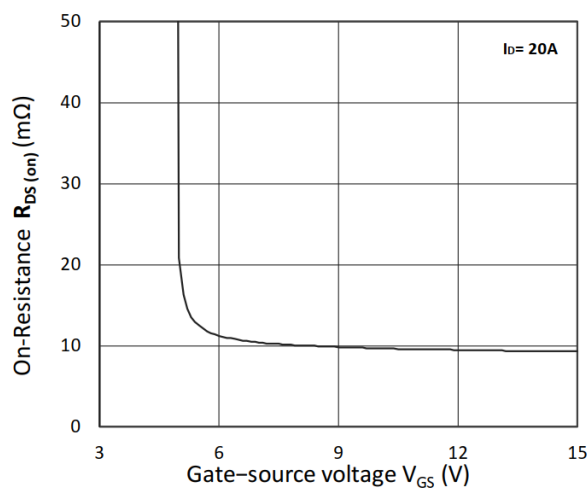


Figure 4. $R_{DS(on)}$ vs. V_{GS}

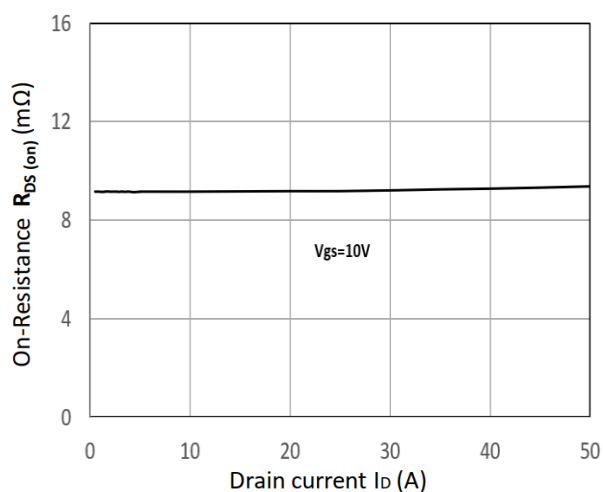


Figure 5. $R_{DS(on)}$ vs. I_D

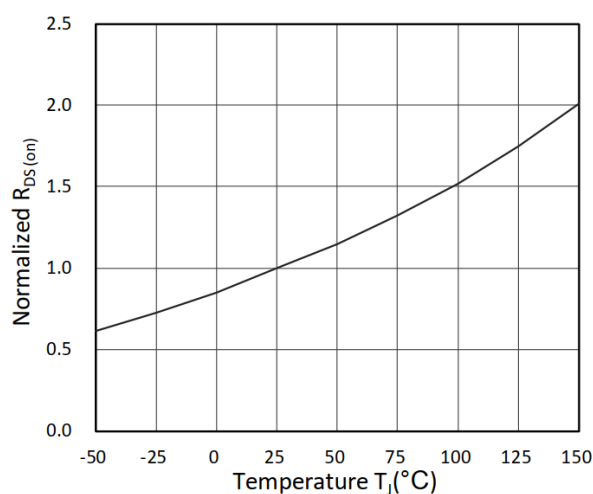


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

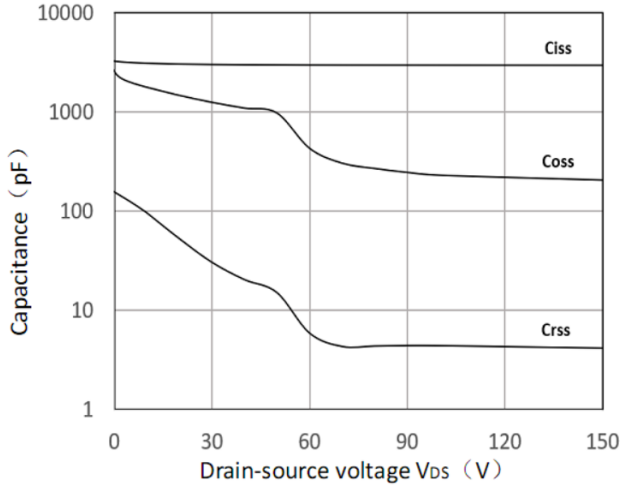


Figure 7. Capacitance Characteristics

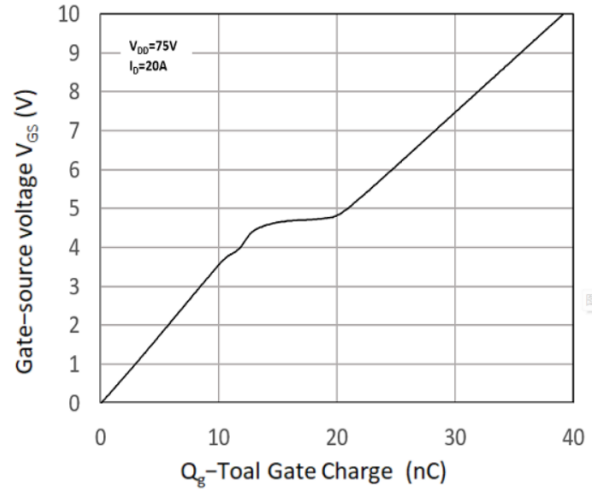


Figure 8. Gate Charge Characteristics

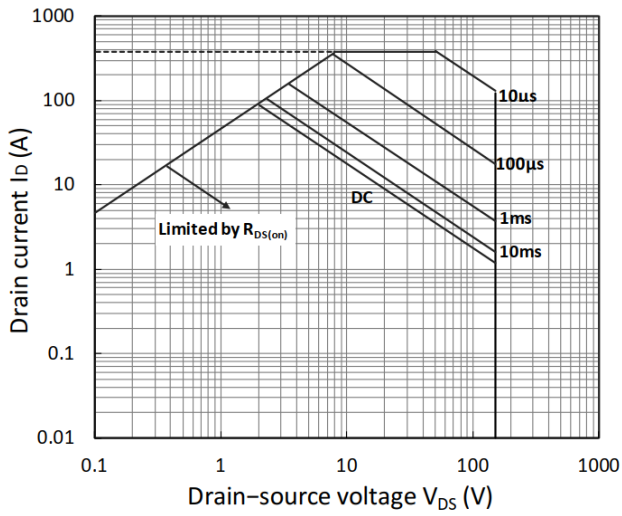


Figure9. Safe Operating Area

Test Circuits and Waveforms

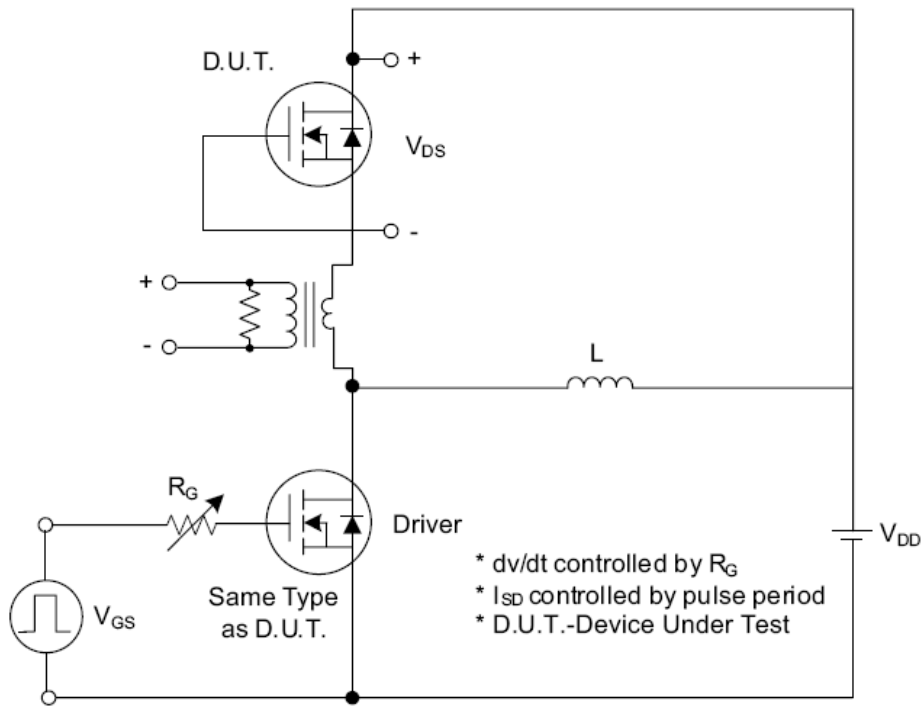


Fig. 1.1 Peak Diode Recovery dv/dt Test Circuit

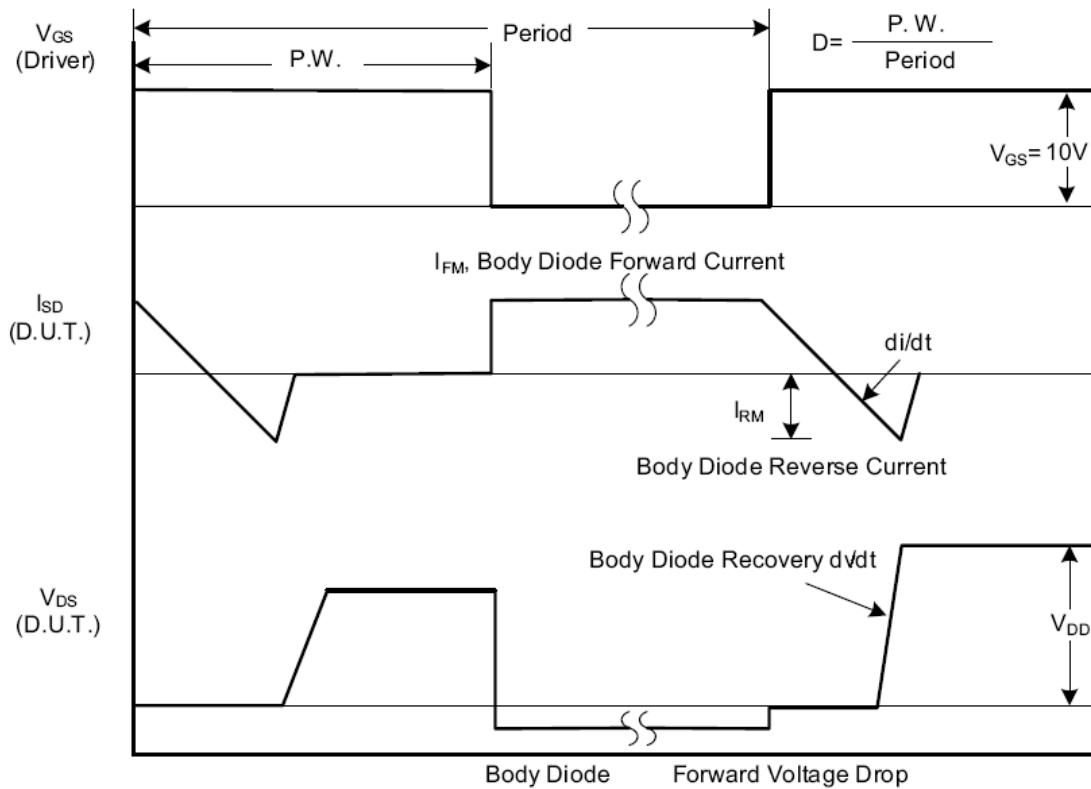


Fig. 1.2 Peak Diode Recovery dv/dt Waveforms

Test Circuits and Waveforms (Cont.)

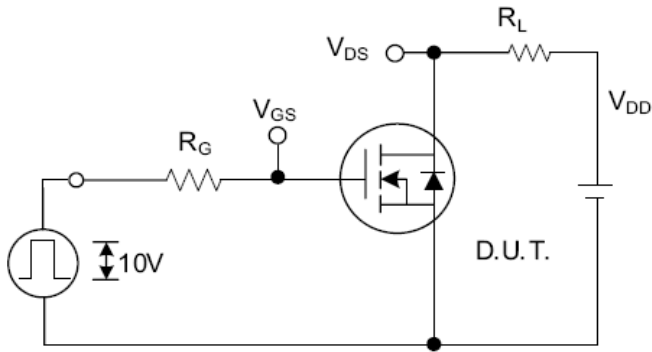


Fig. 2.1 Switching Test Circuit

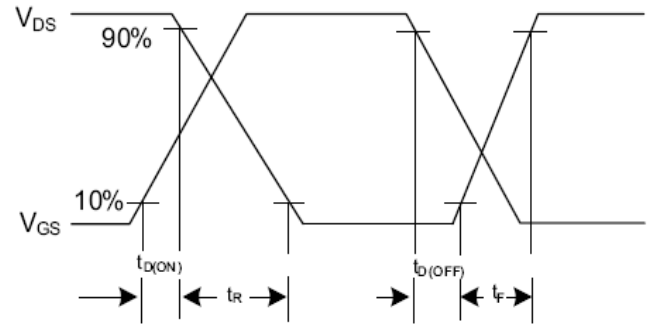


Fig. 2.2 Switching Waveforms

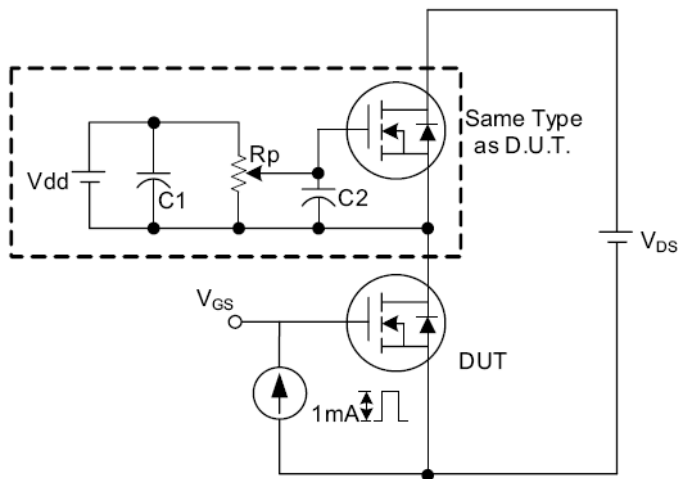


Fig. 3.1 Gate Charge Test Circuit

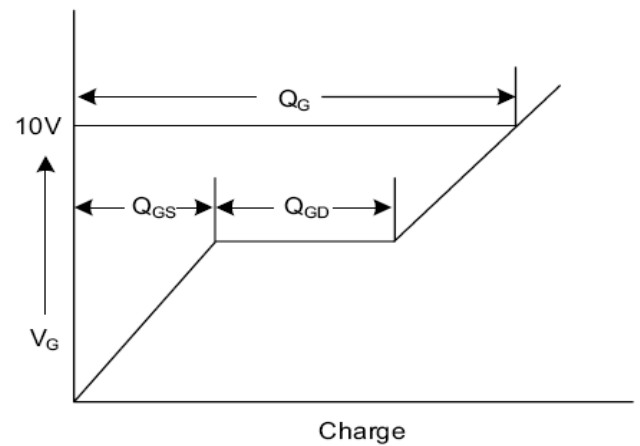


Fig. 3.2 Gate Charge Waveform

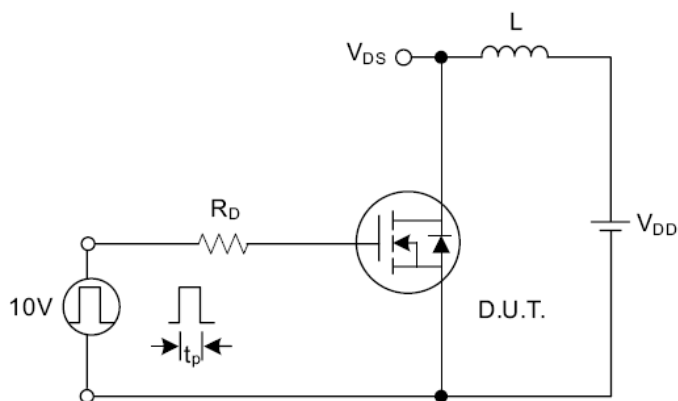


Fig. 4.1 Unclamped Inductive Switching Test Circuit

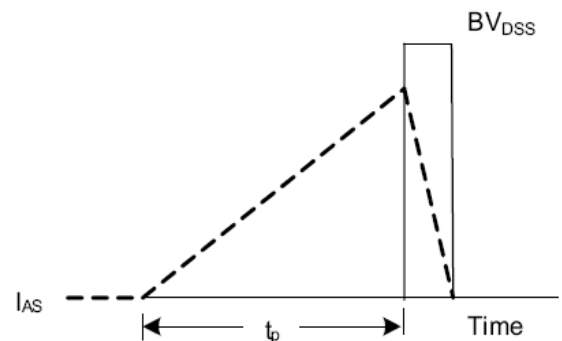


Fig. 4.2 Unclamped Inductive Switching Waveforms

NOTICE

The information presented in this document is for reference only. Involving product optimization and productivity improvement, ChipNobo reserves the right to adjust product indicators and upgrade some technical parameters. ChipNobo is entitled to be exempted from liability for any delay or non-delivery of the information disclosure process that occurs.

本文件中提供的信息仅供参考。涉及产品优化和生产效率改善，ChipNobo 有权调整产品指标和部分技术参数的升级，所出现信息披露过程存在延后或者不能送达的情形，ChipNobo 有获免责权。

The product listed herein is designed to be used with residential and commercial equipment, and do not support sensitive items and specialized equipment in areas where sanctions do exist. ChipNobo Co., Ltd or anyone on its behalf, assumes no responsibility or liability for any damages resulting from improper use.

此处列出的产品旨在民用和商业设备上使用，不支持确有制裁地区的敏感项目和特殊设备，ChipNobo 有限公司或其代表，对因不当使用而造成的任何损害不承担任何责任。

For additional information, please visit our website <http://www.chipnobo.com>, or consult your nearest Chipnobo sales office for further assistance.

欲了解更多信息，请访问我们的网站 <http://www.chipnobo.com>，或咨询离您最近的 Chipnobo 销售办事处以获得进一步帮助。